
HB56UW1673E-A Series

16777216-word $\times$ 72-bit High Density Dynamic RAM Module

HITACHI

ADE-203-823A (Z)

Rev. 1.0

Sep. 17, 1997

Description

The HB56UW1673E-A belongs to 8-byte DIMM (Dual in-line Memory Module) family, and have been developed an optimized main memory solution for 4 and 8-byte processor applications. The HB56UW1673E-A is a 16 M $\times$ 72 Dynamic RAM Module, mounted 18 pieces of 64-Mbit DRAM (HM5165405A) sealed in TSOP package and 2 pieces of 16-bit BiCMOS line driver (74LVT16244) sealed in TSSOP package. The HB56UW1673E-A offers Extended Data Out (EDO) Page Mode as a high speed access mode. An outline of the HB56UW1673E-A is 168-pin socket type package (dual lead out). Therefore, the HB56UW1673E-A makes high density mounting possible without surface mount technology. The HB56UW1673E-A provides common data inputs and outputs. Decoupling capacitors are mounted beside each TSOP on the its module board.

Features

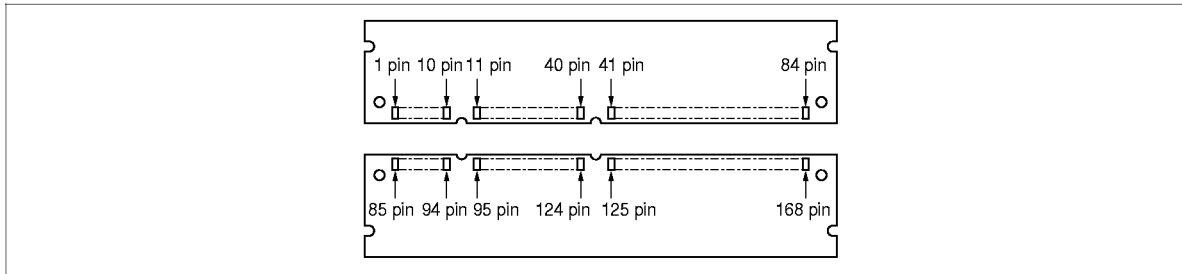
- 168-pin socket type package (Dual lead out)
 - Lead pitch : 1.27 mm
- Single 3.3 V (± 0.3 V)
- High speed
 - Access time: $t_{\text{RAC}} = 60$ ns/70 ns (max)
 - Access time: $t_{\text{CAC}} = 20$ ns/23 ns (max)
- Low power dissipation
 - Active mode: 10.40 W/9.11 W (max)
 - Standby mode (TTL): 166 mW (max)
- Buffered input except $\overline{\text{RAS}}$ and DQ
- 4 byte interleave enabled, dual address input (A0/B0)
- JEDEC standard outline buffered 8-byte DIMM
- EDO page mode capability
- 4096 refresh cycles: 64 ms
- 2 variations of refresh
 - $\overline{\text{RAS}}$ -only refresh
 - $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh
- TTL compatible

HB56UW1673E-A Series

Ordering Information

Type No.	Access time	Package	Contact pad
HB56UW1673E-6A	60 ns	168-pin dual lead out socket type	Gold
HB56UW1673E-7A	70 ns		

Pin Arrangement



Pin No.	Signal name	Pin No.	Signal name	Pin No.	Signal name	Pin No.	Signal name
1	V _{SS}	43	V _{SS}	85	V _{SS}	127	V _{SS}
2	DQ0	44	$\overline{OE}2$	86	DQ36	128	NC
3	DQ1	45	$\overline{RE}2$	87	DQ37	129	NC
4	DQ2	46	$\overline{CE}4$	88	DQ38	130	NC
5	DQ3	47	NC	89	DQ39	131	NC
6	V _{CC}	48	$\overline{WE}2$	90	V _{CC}	132	$\overline{PDE}$
7	DQ4	49	V _{CC}	91	DQ40	133	V _{CC}
8	DQ5	50	NC	92	DQ41	134	NC
9	DQ6	51	NC	93	DQ42	135	NC
10	DQ7	52	DQ18	94	DQ43	136	DQ54
11	DQ8	53	DQ19	95	DQ44	137	DQ55
12	V _{SS}	54	V _{SS}	96	V _{SS}	138	V _{SS}
13	DQ9	55	DQ20	97	DQ45	139	DQ56
14	DQ10	56	DQ21	98	DQ46	140	DQ57
15	DQ11	57	DQ22	99	DQ47	141	DQ58

HB56UW1673E-A Series

Pin Arrangement (cont)

Pin No.	Signal name	Pin No.	Signal name	Pin No.	Signal name	Pin No.	Signal name
16	DQ12	58	DQ23	100	DQ48	142	DQ59
17	DQ13	59	V _{CC}	101	DQ49	143	V _{CC}
18	V _{CC}	60	DQ24	102	V _{CC}	144	DQ60
19	DQ14	61	NC	103	DQ50	145	NC
20	DQ15	62	NC	104	DQ51	146	NC
21	DQ16	63	NC	105	DQ52	147	NC
22	DQ17	64	NC	106	DQ53	148	NC
23	V _{SS}	65	DQ25	107	V _{SS}	149	DQ61
24	NC	66	DQ26	108	NC	150	DQ62
25	NC	67	DQ27	109	NC	151	DQ63
26	V _{CC}	68	V _{SS}	110	V _{CC}	152	V _{SS}
27	$\overline{WE}0$	69	DQ28	111	NC	153	DQ64
28	$\overline{CE}0$	70	DQ29	112	NC	154	DQ65
29	NC	71	DQ30	113	NC	155	DQ66
30	$\overline{RE}0$	72	DQ31	114	NC	156	DQ67
31	$\overline{OE}0$	73	V _{CC}	115	NC	157	V _{CC}
32	V _{SS}	74	DQ32	116	V _{SS}	158	DQ68
33	A0	75	DQ33	117	A1	159	DQ69
34	A2	76	DQ34	118	A3	160	DQ70
35	A4	77	DQ35	119	A5	161	DQ71
36	A6	78	V _{SS}	120	A7	162	V _{SS}
37	A8	79	PD1	121	A9	163	PD2
38	A10	80	PD3	122	A11	164	PD4
39	NC	81	PD5	123	NC	165	PD6
40	V _{CC}	82	PD7	124	V _{CC}	166	PD8
41	NC	83	ID0(V _{SS})	125	NC	167	ID1 (V _{SS})
42	NC	84	V _{CC}	126	B0	168	V _{CC}

HB56UW1673E-A Series

Pin Description

Pin name	Function
A0 to A11, B0	Address input Row address A0 to A11, B0 Column address A0 to A11, B0 Refresh address A0 to A11, B0
DQ0 to DQ71	Data input/output
$\overline{RE}0, \overline{RE}2$	Row address strobe ($\overline{RAS}$)
$\overline{CE}0, \overline{CE}4$	Column address strobe ($\overline{CAS}$)
$\overline{WE}0, \overline{WE}2$	Read/Write enable
$\overline{OE}0, \overline{OE}2$	Output enable
PD1 to PD8	Presence detect
ID0, ID1	ID bit
$\overline{PDE}$	Presence detect Enable
V_{CC}	Power supply
V_{SS}	Ground
NC	No connection

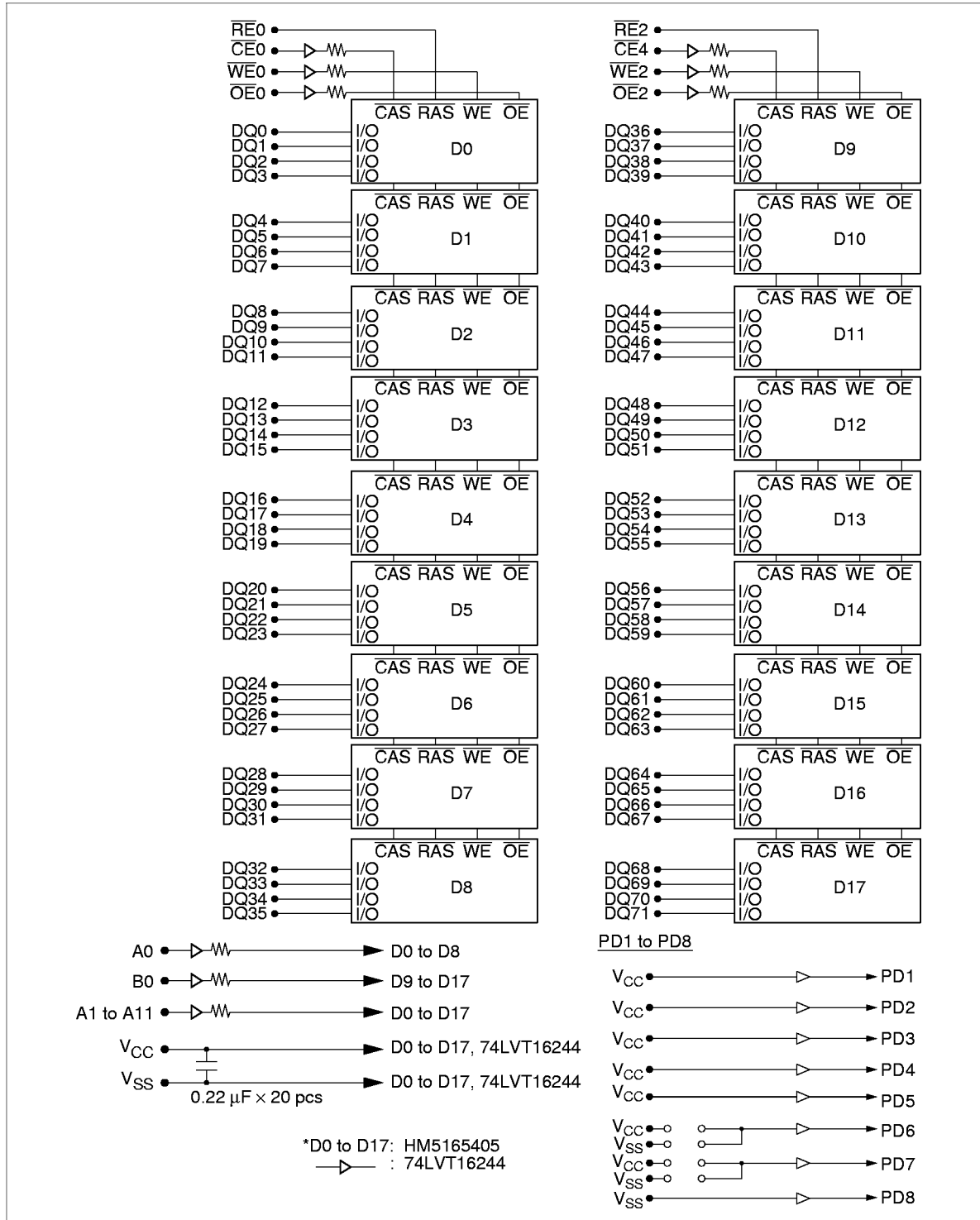
Presence Detect Pin Assignment (Controlled by $\overline{PDE}$ pin)

Pin name	Pin No.	$\overline{PDE} = \text{Low}$		$\overline{PDE} = \text{High}$
		60 ns	70 ns	All
PD1	79	1	1	High-Z
PD2	163	1	1	High-Z
PD3	80	1	1	High-Z
PD4	164	1	1	High-Z
PD5	81	1	1	High-Z
PD6	165	1	0	High-Z
PD7	82	1	1	High-Z
PD8	166	0	0	High-Z

1 : High level (driver output)

0 : Low level (driver output)

Block Diagram



HB56UW1673E-A Series

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Voltage on any pin relative to V_{SS}	V_T	−0.5 to +4.6	V
Supply voltage relative to V_{SS}	V_{CC}	−0.5 to +4.6	V
Short circuit output current	I_{out}	50	mA
Power dissipation	P_T	19	W
Operating temperature	T_{opr}	0 to +70	°C
Storage temperature	T_{stg}	−55 to +125	°C

Recommended DC Operating Conditions ($T_a = 0$ to +70°C)

Parameter	Symbol	Min	Typ	Max	Unit	Notes
Supply voltage	V_{SS}	0	0	0	V	
	V_{CC}	3.0	3.3	3.6	V	1
Input high voltage	V_{IH}	2.0	—	$V_{CC} + 0.3$	V	1
Input low voltage	V_{IL}	−0.3	—	0.8	V	1

Note: 1. All voltage referred to V_{SS} .

HB56UW1673E-A Series

DC Characteristics ($T_a = 0$ to $+70^\circ\text{C}$, $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$, $V_{SS} = 0 \text{ V}$)

HB56UW1673E-A							
Parameter	Symbol	60 ns		70 ns		Unit	Test conditions
		Min	Max	Min	Max		
Operating current*1, *2	I _{CC1}	—	2890	—	2530	mA	t _{RC} = min
Standby current	I _{CC2}	—	46	—	46	mA	TTL interface RAS, CAS = V _{IH} Dout = High-Z
		—	28	—	28	mA	CMOS interface RAS, CAS ≥ V _{CC} − 0.2 V Dout = High-Z
RAS-only refresh current*2	I _{CC3}	—	2890	—	2530	mA	t _{RC} = min
Standby current*1	I _{CC5}	—	100	—	100	mA	RAS = V _{IH} , CAS = V _{IL} Dout = enable
CAS-before-RAS refresh current	I _{CC6}	—	2530	—	2170	mA	t _{RC} = min
EDO page mode current*1, *3	I _{CC7}	—	2170	—	1900	mA	t _{HPC} = min
Input leakage current	I _{LI}	−10	10	−10	10	μA	0 V ≤ Vin ≤ V _{CC} + 0.3 V
Output leakage current	I _{LO}	−10	10	−10	10	μA	0 V ≤ Vout ≤ V _{CC} Dout = disable
Output high voltage	V _{OH}	2.4	V _{CC}	2.4	V _{CC}	V	High Iout = −2 mA
Output low voltage	V _{OL}	0	0.4	0	0.4	V	Low Iout = 2 mA

Notes : 1. I_{CC} depends on output load condition when the device is selected. I_{CC} max is specified at the output open condition.

2. Address can be changed once or less while $\overline{\text{RAS}} = V_{IL}$.

3. Address can be changed once or less within one page mode cycle t_{HPC} .

Capacitance ($T_a = 25^\circ\text{C}$, $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$)

Parameter	Symbol	Typ	Max	Unit	Notes
Input capacitance (Address)	C_{I1}	—	20	pF	1
Input capacitance ($\overline{\text{CAS}}$, $\overline{\text{WE}}$, $\overline{\text{OE}}$)	C_{I2}	—	20	pF	1
Input capacitance ($\overline{\text{RAS}}$)	C_{I3}	—	78	pF	1
I/O capacitance (DQ)	$C_{I/O}$	—	20	pF	1, 2

Notes : 1. Capacitance measured with Boonton Meter or effective capacitance measuring method.

2. $\overline{\text{CAS}} = V_{IH}$ to disable Dout.

HB56UW1673E-A Series

AC Characteristics ($T_a = 0$ to $+70^\circ\text{C}$, $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$, $V_{SS} = 0 \text{ V}$) *¹, *², *¹⁷

Test Conditions

- Input rise and fall times: 2 ns
- Input levels: $V_{IL} = 0 \text{ V}$, $V_{IH} = 3.0 \text{ V}$
- Input timing reference levels: 0.8 V, 2.0 V
- Output timing reference levels: 0.8 V, 2.0 V
- Output load: 1 TTL gate + C_L (100 pF) (Including scope and jig)

Read, Write, Read-Modify-Write and Refresh Cycles (Common parameters)

		HB56UW1673E-A					
		60 ns		70 ns			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Random read or write cycle time	t _{RC}	104	—	124	—	ns	
$\overline{\text{RAS}}$ precharge time	t _{RP}	40	—	50	—	ns	
$\overline{\text{CAS}}$ precharge time	t _{CP}	10	—	13	—	ns	
$\overline{\text{RAS}}$ pulse width	t _{RAS}	60	10000	70	10000	ns	
$\overline{\text{CAS}}$ pulse width	t _{CAS}	10	10000	13	10000	ns	
Row address setup time	t _{ASR}	5	—	5	—	ns	
Row address hold time	t _{RAH}	10	—	10	—	ns	
Column address setup time	t _{ASC}	0	—	0	—	ns	
Column address hold time	t _{CAH}	10	—	13	—	ns	
$\overline{\text{RAS}}$ to $\overline{\text{CAS}}$ delay time	t _{RCD}	20	40	20	47	ns	3
$\overline{\text{RAS}}$ to column address delay time	t _{RAD}	14	25	15	30	ns	4
$\overline{\text{RAS}}$ hold time	t _{RSH}	20	—	23	—	ns	
$\overline{\text{CAS}}$ hold time	t _{CSH}	48	—	58	—	ns	21
$\overline{\text{CAS}}$ to $\overline{\text{RAS}}$ precharge time	t _{CRP}	10	—	10	—	ns	
$\overline{\text{OE}}$ to Din delay time	t _{OED}	20	—	23	—	ns	5
$\overline{\text{OE}}$ delay time from Din	t _{DZO}	0	—	0	—	ns	6
$\overline{\text{CAS}}$ delay time from Din	t _{DZC}	0	—	0	—	ns	6
Transition time (rise and fall)	t _T	2	50	2	50	ns	7

HB56UW1673E-A Series

Read Cycle

		HB56UW1673E-A					
		60 ns		70 ns			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Access time from $\overline{\text{RAS}}$	t_{RAC}	—	60	—	70	ns	8, 9
Access time from $\overline{\text{CAS}}$	t_{CAC}	—	20	—	23	ns	9, 10, 16
Access time from address	t_{AA}	—	35	—	40	ns	9, 11, 16
Access time from $\overline{\text{OE}}$	t_{OEA}	—	20	—	23	ns	9
Read command setup time	t_{RCS}	0	—	0	—	ns	
Read command hold time to $\overline{\text{CAS}}$	t_{RCH}	0	—	0	—	ns	12
Read command hold time from $\overline{\text{RAS}}$	t_{RCHR}	60	—	70	—	ns	
Read command hold time to $\overline{\text{RAS}}$	t_{RRH}	0	—	0	—	ns	12
Column address to $\overline{\text{RAS}}$ lead time	t_{RAL}	35	—	40	—	ns	
Column address to $\overline{\text{CAS}}$ lead time	t_{CAL}	18	—	23	—	ns	
$\overline{\text{CAS}}$ to output in low-Z	t_{CLZ}	2	—	2	—	ns	
Output data hold time	t_{OH}	3	—	3	—	ns	20
Output data hold time from $\overline{\text{OE}}$	t_{OHO}	3	—	3	—	ns	
Output buffer turn-off time	t_{OFF}	—	20	—	20	ns	13, 20
Output buffer turn-off to $\overline{\text{OE}}$	t_{OEZ}	—	20	—	20	ns	13
$\overline{\text{CAS}}$ to Din delay time	t_{CDD}	20	—	23	—	ns	5
Output data hold time from $\overline{\text{RAS}}$	t_{OHR}	3	—	3	—	ns	20
Output buffer turn-off to $\overline{\text{RAS}}$	t_{OFR}	—	15	—	15	ns	13, 20
Output buffer turn-off to $\overline{\text{WE}}$	t_{WEZ}	—	20	—	20	ns	13
$\overline{\text{WE}}$ to Din delay time	t_{WED}	20	—	23	—	ns	
$\overline{\text{RAS}}$ to Din delay time	t_{RDD}	15	—	18	—	ns	

HB56UW1673E-A Series

Write Cycle

		HB56UW1673E-A					
		60 ns		70 ns			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Write command setup time	t _{WCS}	0	—	0	—	ns	14
Write command hold time	t _{WCH}	10	—	13	—	ns	
Write command pulse width	t _{WP}	10	—	10	—	ns	
Write command to $\overline{RAS}$ lead time	t _{RWL}	20	—	23	—	ns	
Write command to $\overline{CAS}$ lead time	t _{CWL}	10	—	13	—	ns	
Data-in setup time	t _{DS}	0	—	0	—	ns	
Data-in hold time	t _{DH}	15	—	18	—	ns	

Read-Modify-Write Cycle

		HB56UW1673E-A					
		60 ns		70 ns			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
Read-modify-write cycle time	t _{RWC}	154	—	180	—	ns	
RAS to $\overline{WE}$ delay time	t _{RWD}	83	—	96	—	ns	14
CAS to $\overline{WE}$ delay time	t _{CWD}	33	—	39	—	ns	14
Column address to $\overline{WE}$ delay time	t _{AWD}	48	—	56	—	ns	14
$\overline{OE}$ hold time from $\overline{WE}$	t _{OEh}	15	—	18	—	ns	

Refresh Cycle

		HB56UW1673E-A					
		60 ns		70 ns			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
CAS setup time (CBR refresh cycle)	t _{CSR}	10	—	10	—	ns	
CAS hold time (CBR refresh cycle)	t _{CHR}	10	—	10	—	ns	
WE setup time (CBR refresh cycle)	t _{WRP}	5	—	5	—	ns	
WE hold time (CBR refresh cycle)	t _{WRH}	10	—	10	—	ns	
RAS precharge to CAS hold time	t _{RPC}	0	—	0	—	ns	

EDO Page Mode Cycle

		HB56UW1673E-A					
		60 ns		70 ns			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
EDO page mode cycle time	t _{HPC}	25	—	30	—	ns	19
EDO page mode $\overline{\text{RAS}}$ pulse width	t _{RASP}	—	100000	—	100000	ns	15
Access time from $\overline{\text{CAS}}$ precharge	t _{CPA}	—	40	—	45	ns	9, 16
$\overline{\text{RAS}}$ hold time from $\overline{\text{CAS}}$ precharge	t _{CPRH}	40	—	45	—	ns	
Output data hold time from $\overline{\text{CAS}}$ low	t _{DOH}	3	—	3	—	ns	9
$\overline{\text{CAS}}$ hold time referred $\overline{\text{OE}}$	t _{COL}	10	—	13	—	ns	
$\overline{\text{CAS}}$ to $\overline{\text{OE}}$ setup time	t _{COP}	10	—	10	—	ns	
Read command hold time from $\overline{\text{CAS}}$ precharge	t _{RCHC}	35	—	40	—	ns	
Write pulse width during $\overline{\text{CAS}}$ precharge	t _{WPE}	10	—	10	—	ns	
$\overline{\text{OE}}$ precharge time	t _{OEP}	10	—	10	—	ns	

EDO Page Mode Read-Modify-Write Cycle

		HB56UW1673E-A					
		60 ns		70 ns			
Parameter	Symbol	Min	Max	Min	Max	Unit	Notes
EDO page mode read- modify-write cycle time	t _{HPRWC}	68	—	79	—	ns	
$\overline{WE}$ delay time from $\overline{CAS}$ precharge	t _{CPW}	54	—	62	—	ns	14

HB56UW1673E-A Series

Refresh

Parameter	Symbol	Max	Unit	Notes
Refresh period	t_{REF}	64	ms	4096 cycles

Notes: 1. AC measurements assume $t_T = 2$ ns.

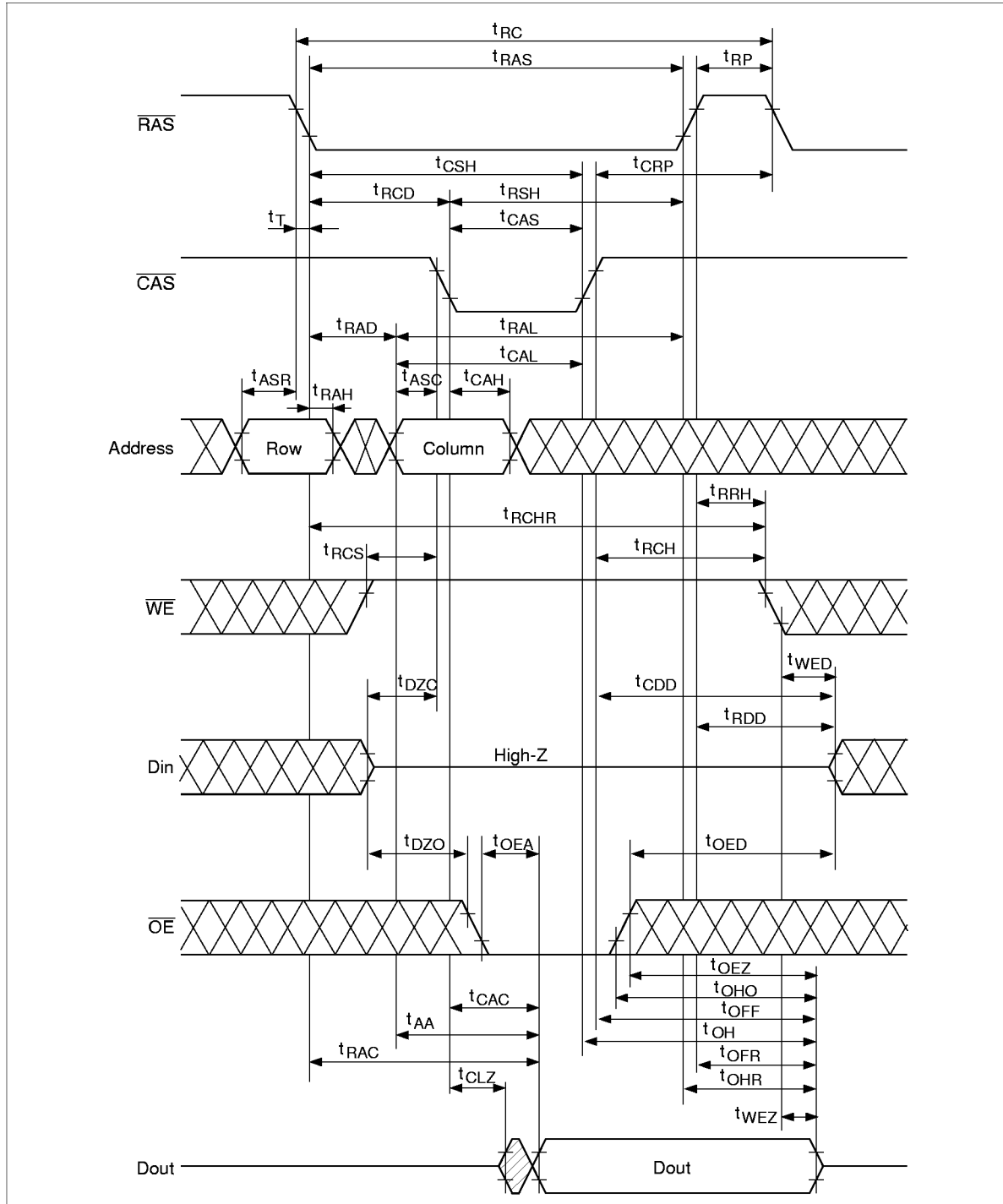
2. An initial pause of 200 μ s is required after power up followed by a minimum of eight initialization cycles (any combination of cycles containing RAS-only refresh or CAS-before-RAS refresh).
3. Operation with the t_{RCD} (max) limit insures that t_{RAC} (max) can be met, t_{RCD} (max) is specified as a reference point only; if t_{RCD} is greater than the specified t_{RCD} (max) limit, then access time is controlled exclusively by t_{CAC} .
4. Operation with the t_{RAD} (max) limit insures that t_{RAC} (max) can be met, t_{RAD} (max) is specified as a reference point only; if t_{RAD} is greater than the specified t_{RAD} (max) limit, then access time is controlled exclusively by t_{AA} .
5. Either t_{OED} or t_{CDD} must be satisfied.
6. Either t_{DZO} or t_{DZC} must be satisfied.
7. V_{IH} (min) and V_{IL} (max) are reference levels for measuring timing of input signals. Also, transition times are measured between V_{IH} (min) and V_{IL} (max).
8. Assumes that $t_{RCD} \leq t_{RCD}$ (max) and $t_{RAD} \leq t_{RAD}$ (max). If t_{RCD} or t_{RAD} is greater than the maximum recommended value shown in this table, t_{RAC} exceeds the value shown.
9. Measured with a load circuit equivalent to 1TTL loads and 100 pF.
10. Assumes that $t_{RCD} \geq t_{RCD}$ (max) and $t_{RCD} + t_{CAC}$ (max) $\geq t_{RAD} + t_{AA}$ (max).
11. Assumes that $t_{RAD} \geq t_{RAD}$ (max) and $t_{RCD} + t_{CAC}$ (max) $\leq t_{RAD} + t_{AA}$ (max).
12. Either t_{RCH} or t_{RRH} must be satisfied for a read cycles.
13. t_{OFF} (max), t_{OEZ} (max), t_{WEZ} (max) and t_{OFFR} (max) define the time at which the outputs achieve the open circuit condition and are not referred to output voltage levels.
14. t_{WCS} , t_{RWD} , t_{CWD} , t_{AWD} and t_{CPW} are not restrictive operating parameters. They are included in the data sheet as electrical characteristics only; if $t_{WCS} \geq t_{WCS}$ (min), the cycle is an early write cycle and the data out pin will remain open circuit (high impedance) throughout the entire cycle; if $t_{RWD} \geq t_{RWD}$ (min), $t_{CWD} \geq t_{CWD}$ (min), and $t_{AWD} \geq t_{AWD}$ (min), or $t_{CWD} \geq t_{CWD}$ (min), $t_{AWD} \geq t_{AWD}$ (min), and $t_{CPW} \geq t_{CPW}$ (min), the cycle is a read-modify-write and the data output will contain data read from the selected cell; if neither of the above sets of conditions is satisfied, the condition of the data out (at access time) is indeterminate.
15. t_{RASP} defines $\overline{RAS}$ pulse width in EDO page mode cycles.
16. Access time is determined by the longest among t_{AA} , t_{CAC} and t_{CPA} .
17. All the V_{CC} and V_{SS} pin shall be supplied with the same voltages.
18. In delayed write or read-modify-write cycles, $\overline{OE}$ must disable output buffer prior to applying data to the device.
19. t_{HPC} (min) can be achieved during a series of EDO page mode write cycles or EDO page mode read cycles. If both write and read operation are mixed in a EDO page mode $\overline{RAS}$ cycle (EDO page mode mix cycle (1), (2)), minimum value of $\overline{CAS}$ cycle ($t_{CAS} + t_{CP} + 2t_T$) becomes greater than the specified t_{HPC} (min) value. The value of $\overline{CAS}$ cycle time of mixed EDO page mode is shown in EDO page mode mix cycle (1) and (2).

20. Data output turns off and becomes high impedance from later rising edge of $\overline{\text{RAS}}$ and $\overline{\text{CAS}}$.
Hold time and turn off time are specified by the timing specifications of later rising edge of $\overline{\text{RAS}}$ and $\overline{\text{CAS}}$ between t_{OHR} and t_{OH} and between t_{OFR} and t_{OFF} .
21. t_{CSH} (min) can be achieved when $t_{\text{RCD}} \leq t_{\text{CSH}}$ (min) - t_{CAS} (min).
22. XXX: H or L (H: V_{IH} (min) $\leq V_{\text{IN}} \leq V_{\text{IH}}$ (max), L: V_{IL} (min) $\leq V_{\text{IN}} \leq V_{\text{IL}}$ (max))
/////: Invalid Dout
- When the address, clock and input pins are not described on timing waveforms, their pins must be applied V_{IH} or V_{IL} .

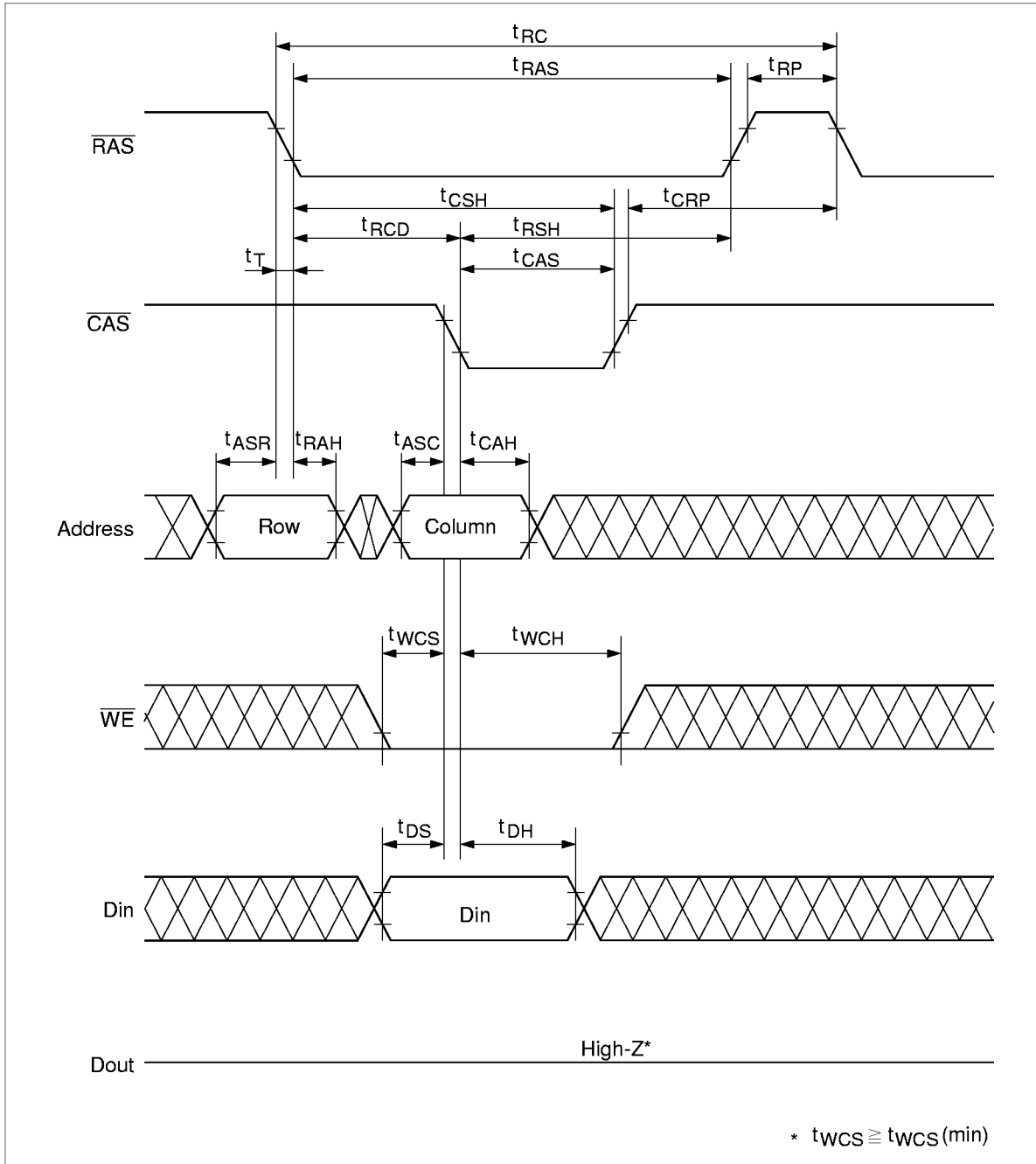
HB56UW1673E-A Series

Timing Waveforms*22

Read Cycle

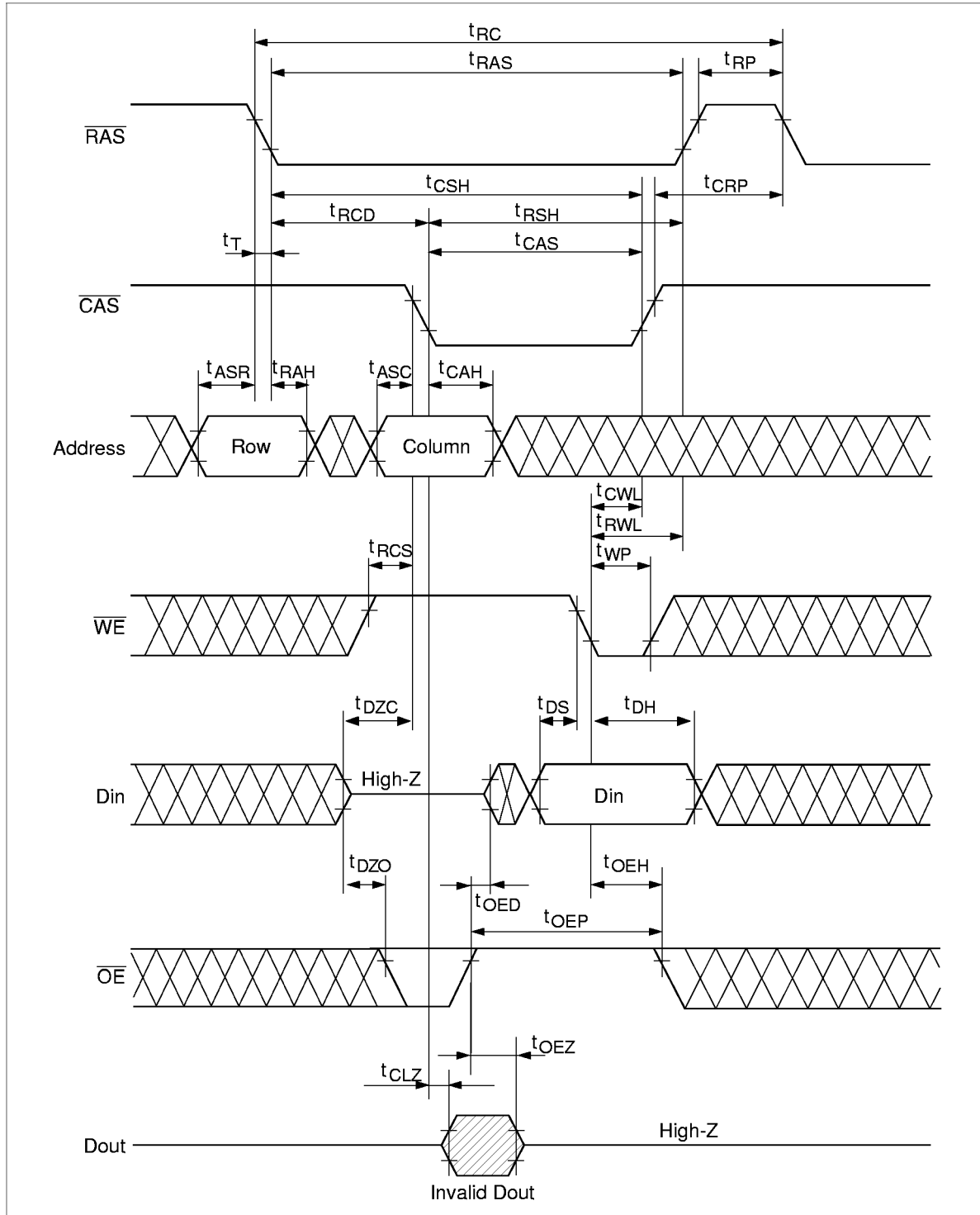


Early Write Cycle

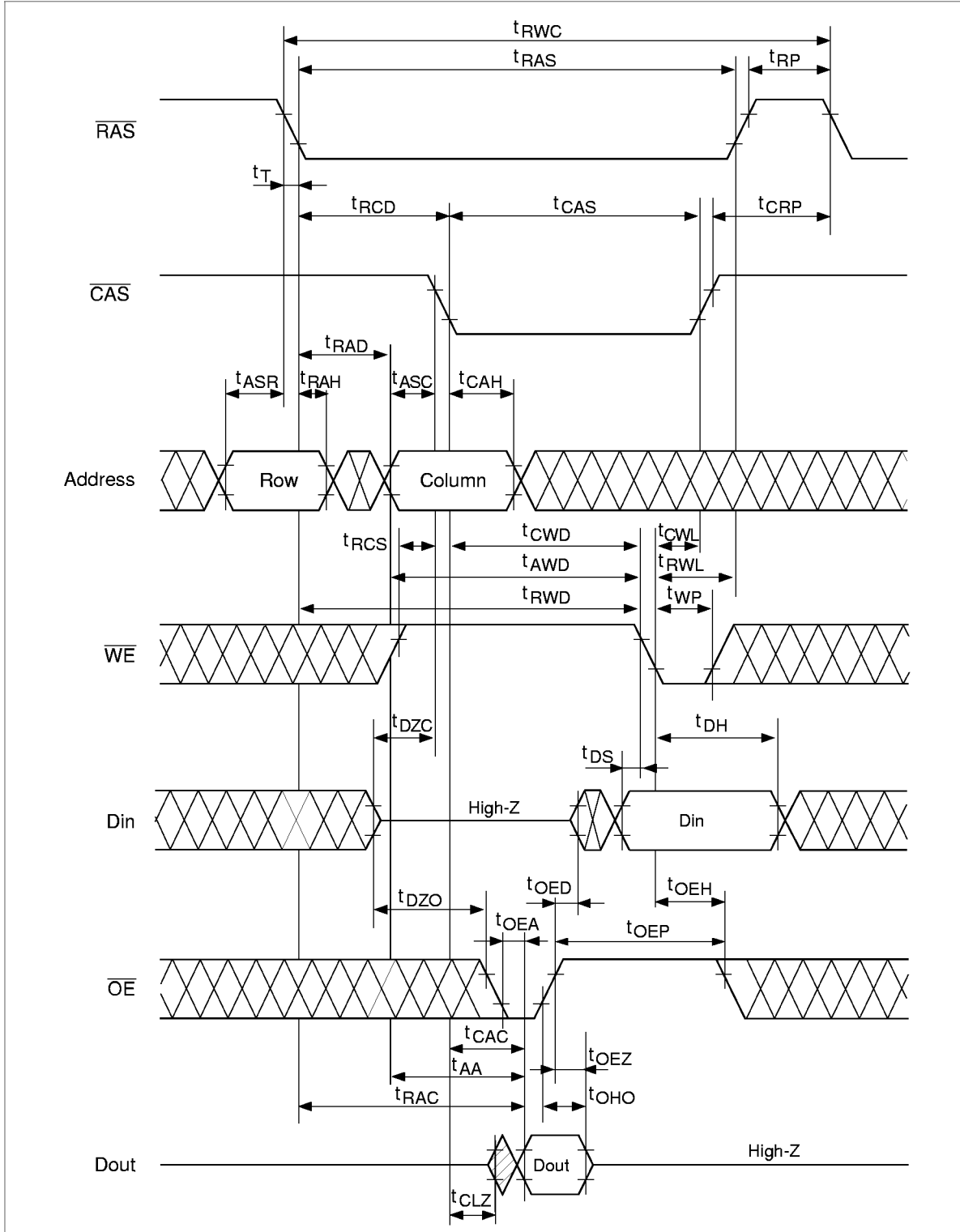


HB56UW1673E-A Series

Delayed Write Cycle*18

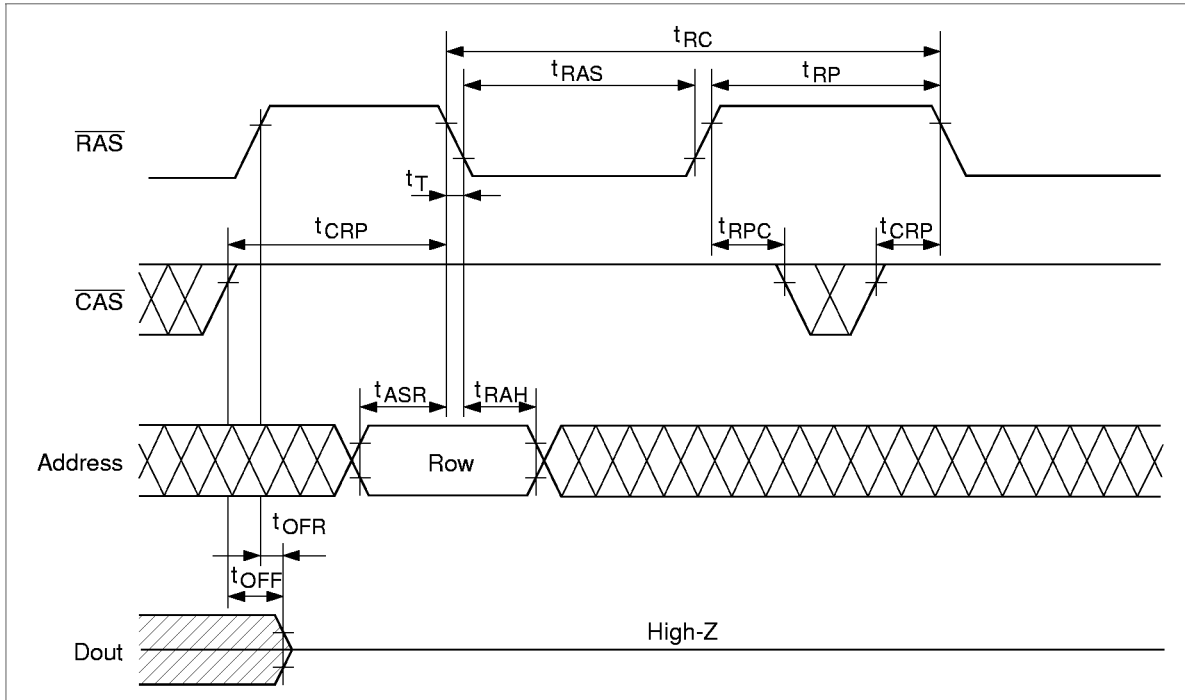


Read-Modify-Write Cycle*18

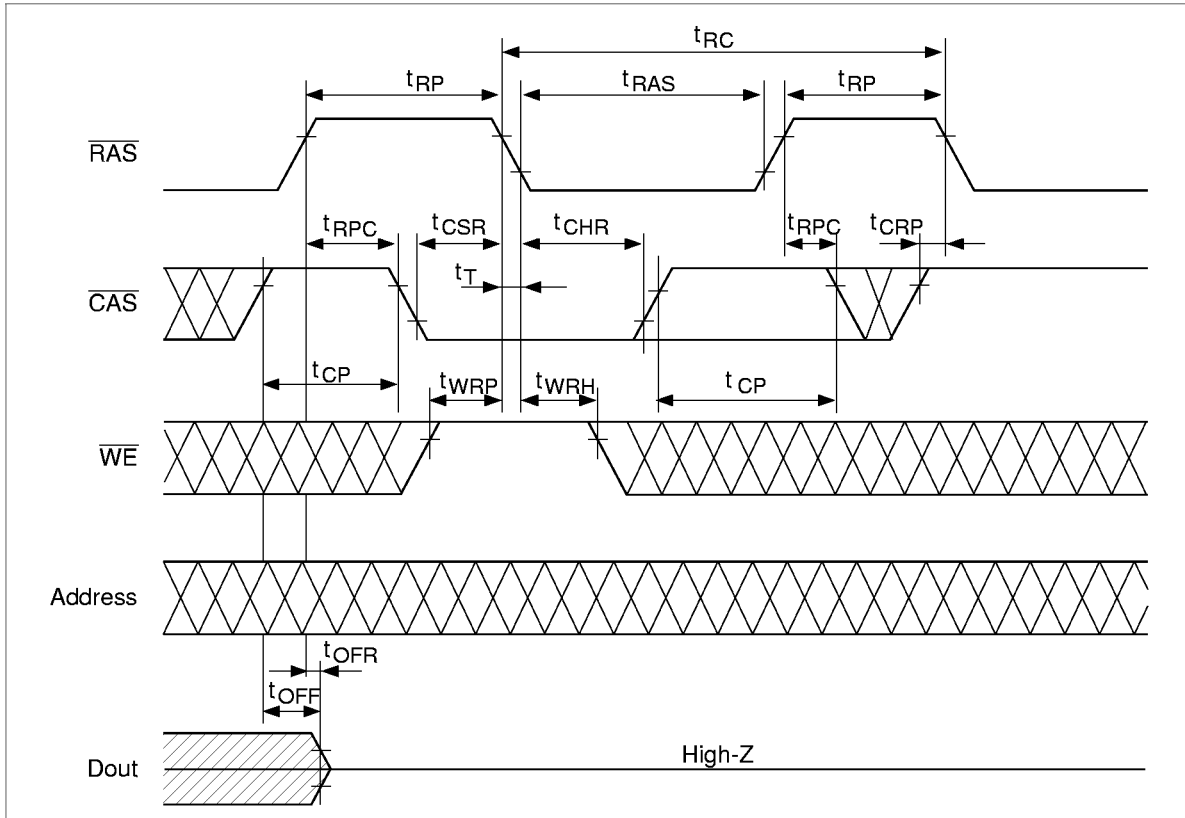


HB56UW1673E-A Series

$\overline{\text{RAS}}$ -Only Refresh Cycle

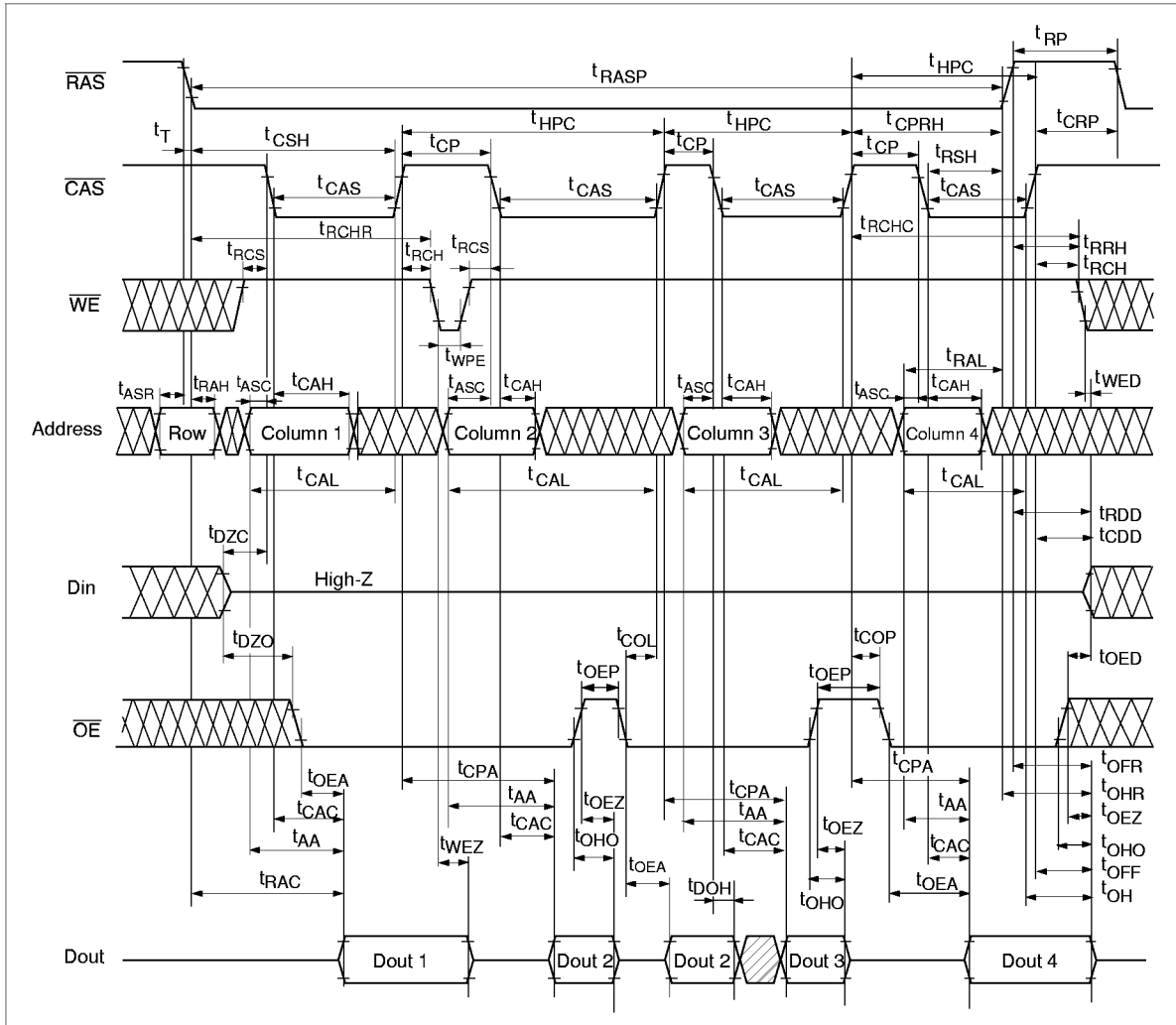


CAS-Before-RAS Refresh Cycle

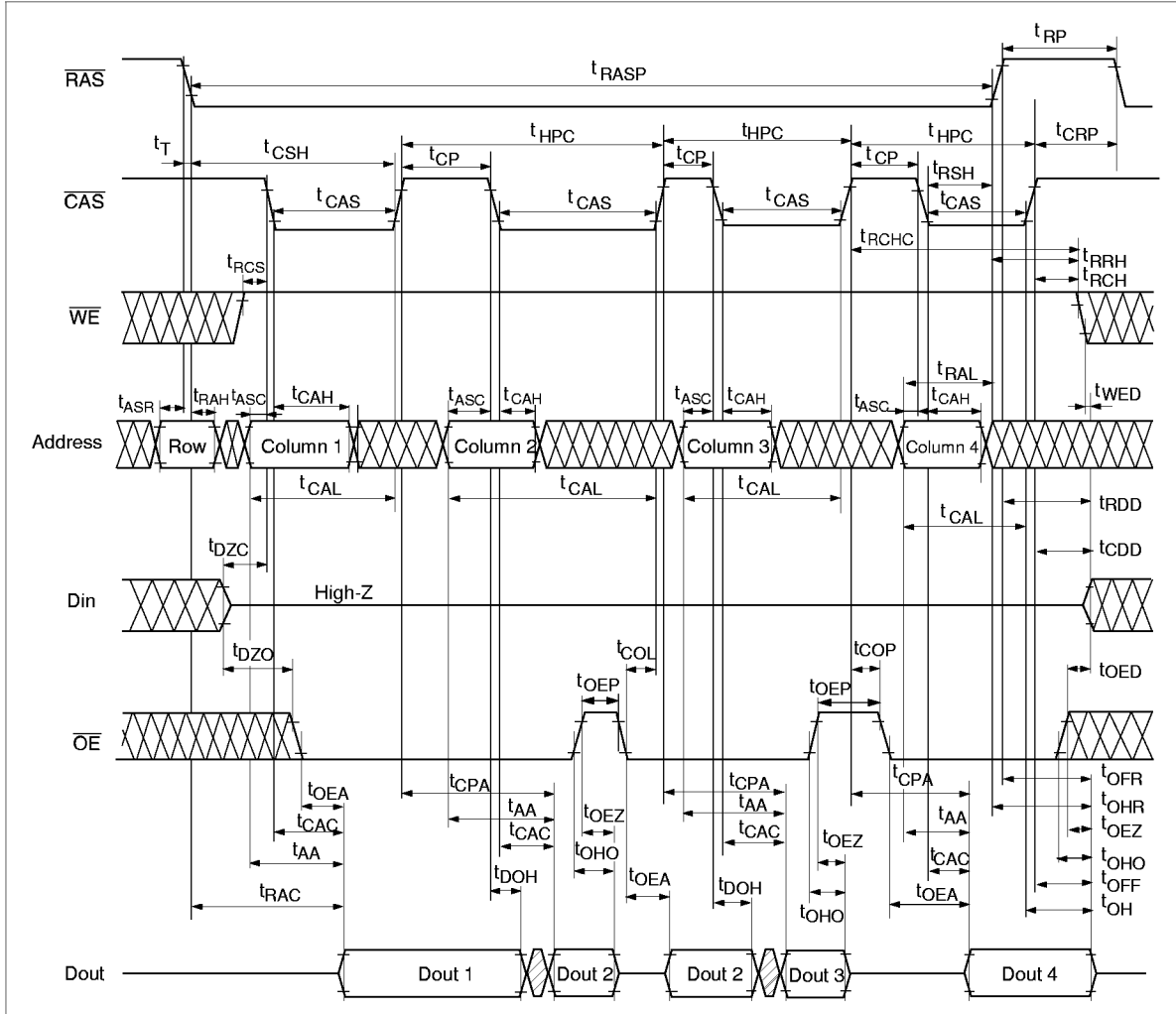


HB56UW1673E-A Series

EDO Page Mode Read Cycle (1)

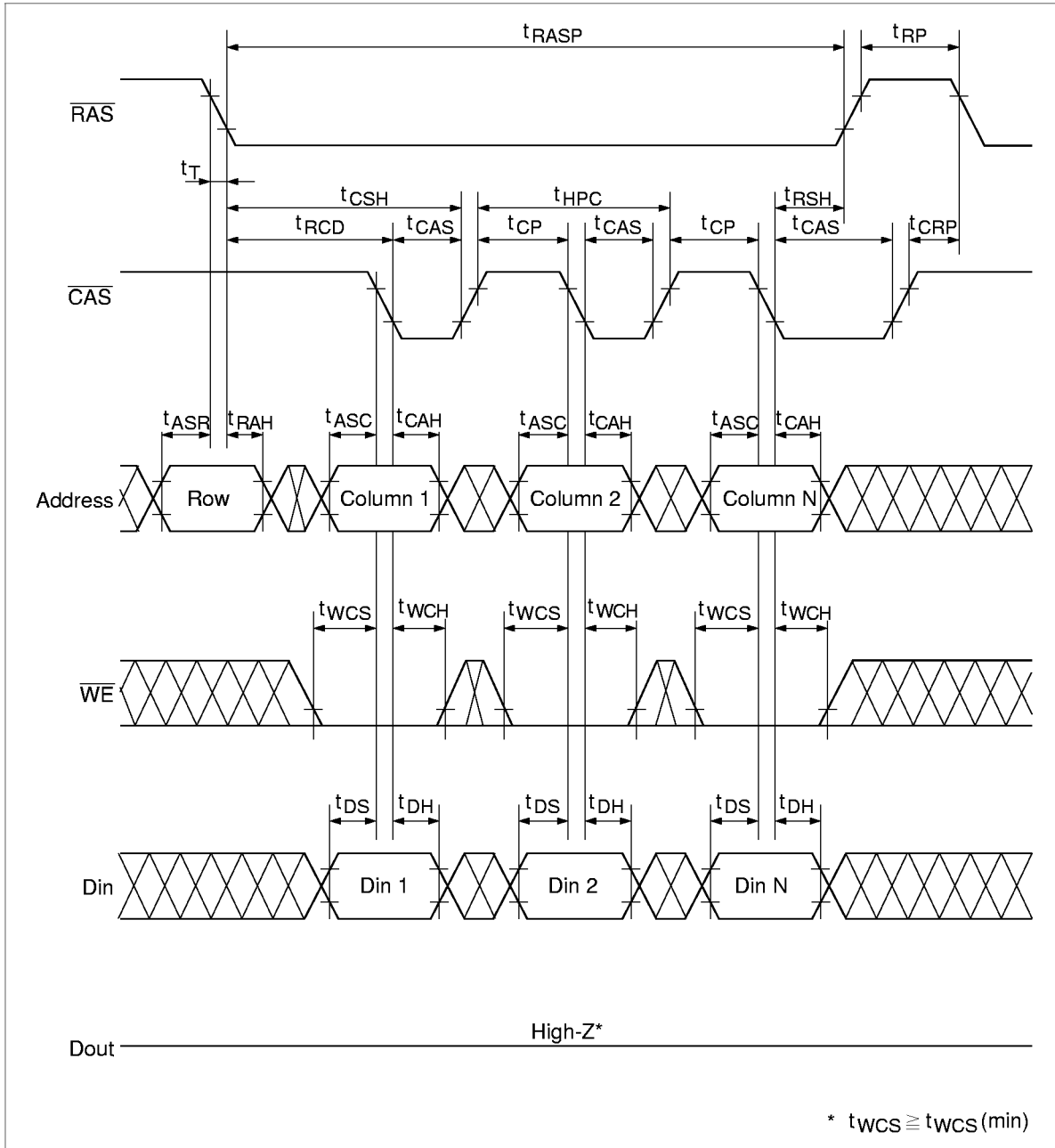


EDO Page Mode Read Cycle (2)

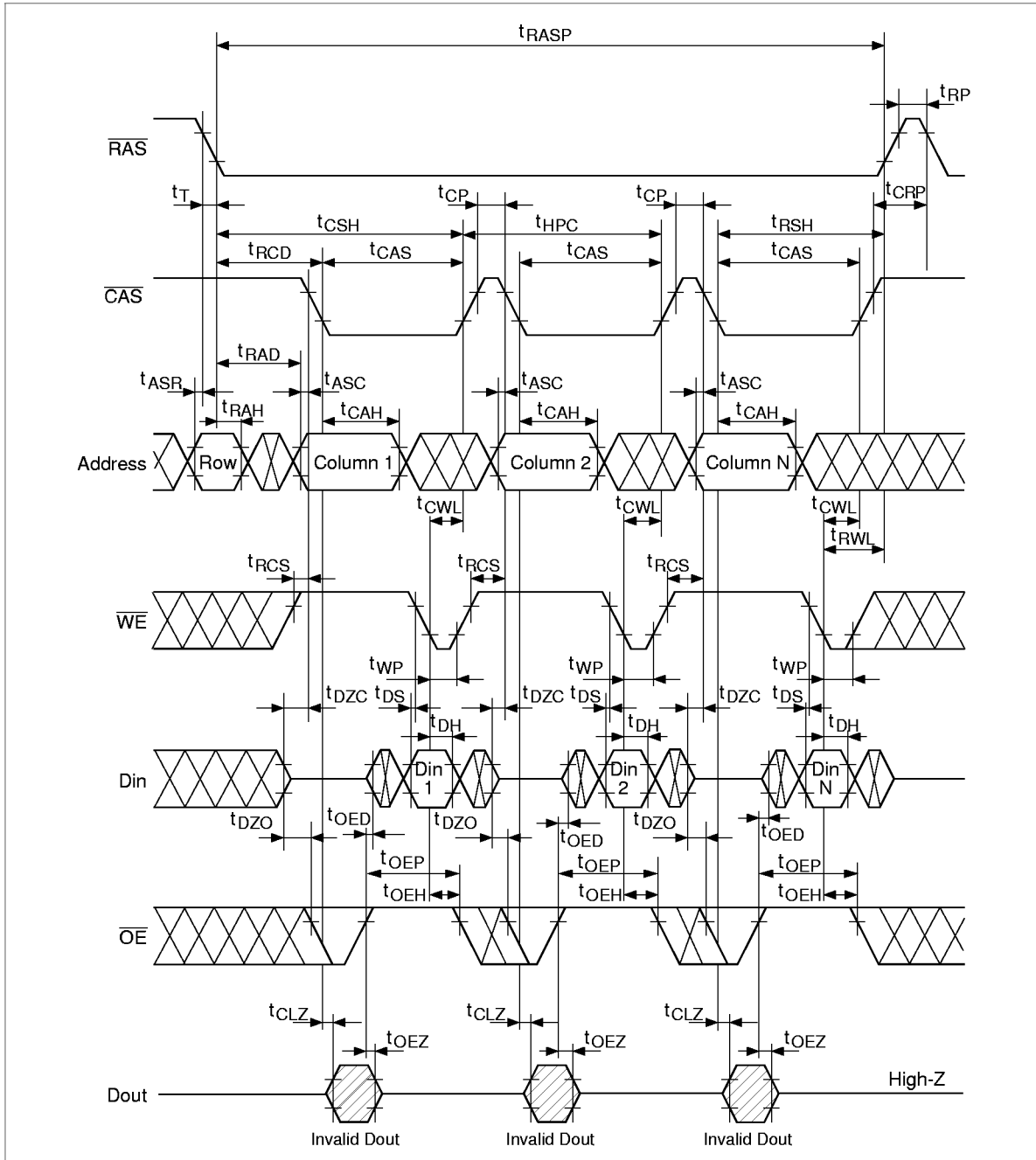


HB56UW1673E-A Series

EDO Page Mode Early Write Cycle

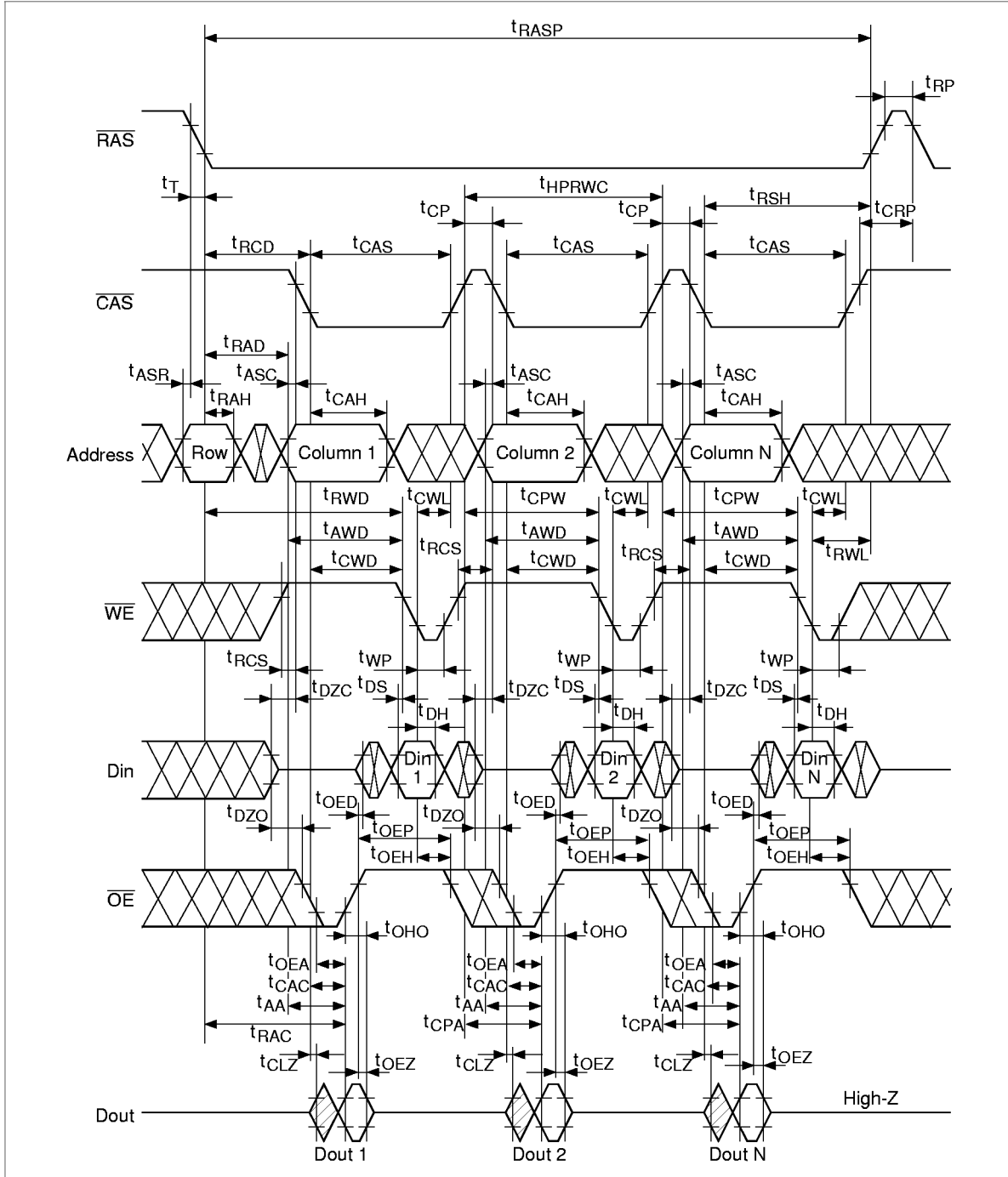


EDO Page Mode Delayed Write Cycle*18



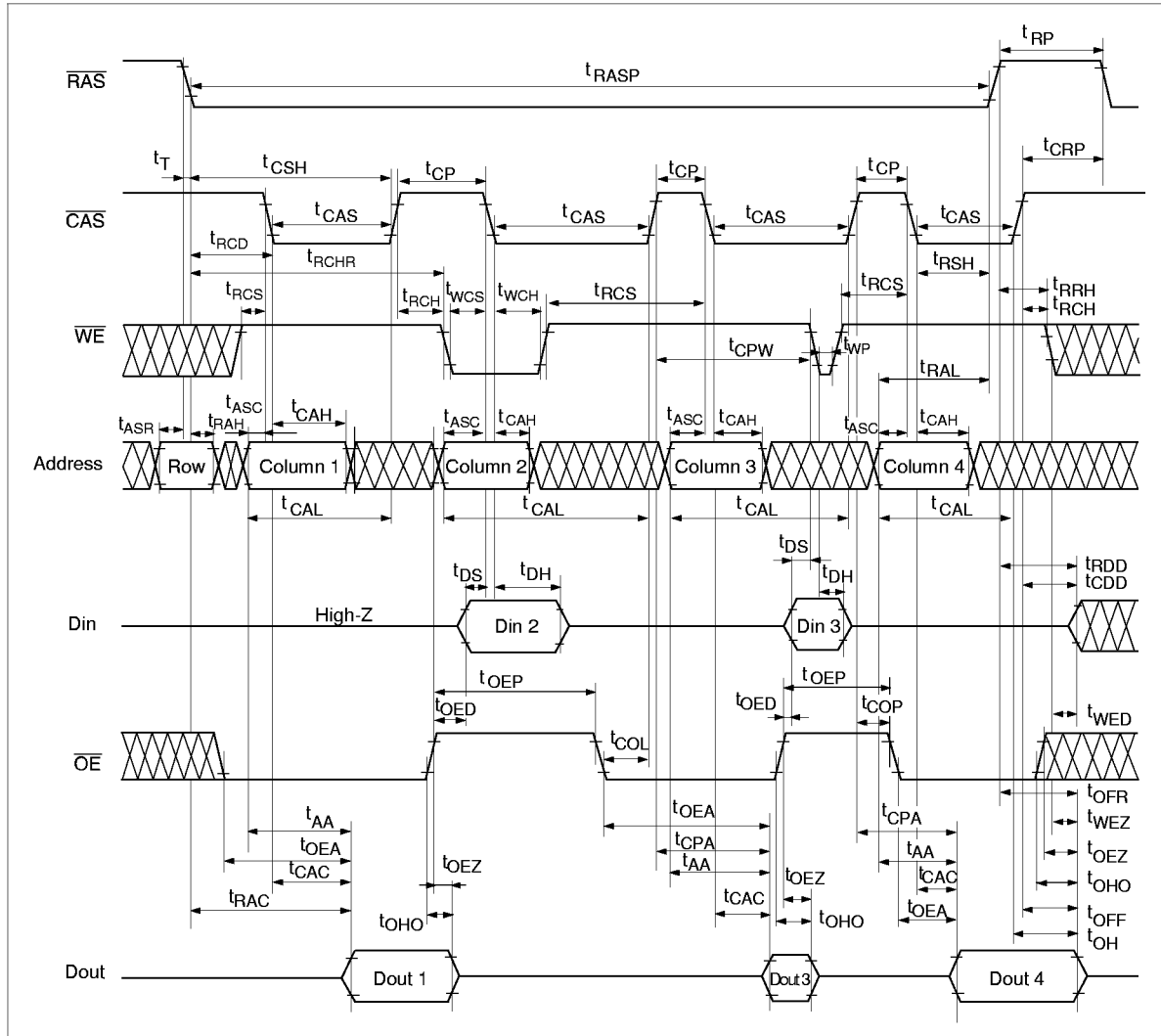
HB56UW1673E-A Series

EDO Page Mode Read-Modify-Write Cycle*18



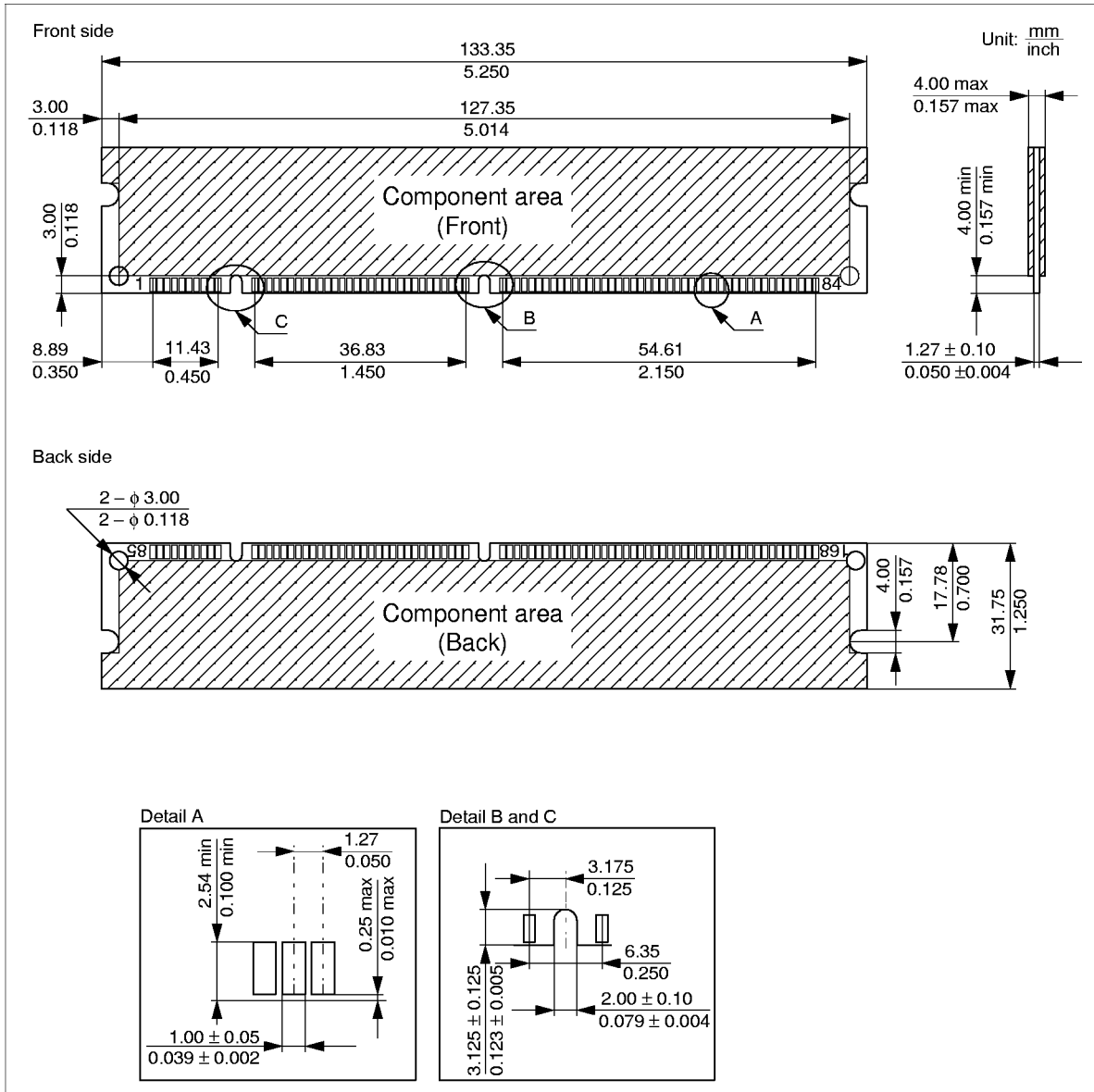
HB56UW1673E-A Series

EDO Page Mode Mix Cycle (2)*19



Physical Outline

HB56UW1673E-A Series



HB56UW1673E-A Series

When using this document, keep the following in mind:

1. This document may, wholly or partially, be subject to change without notice.
2. All rights are reserved: No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without Hitachi's permission.
3. Hitachi will not be held responsible for any damage to the user that may result from accidents or any other reasons during operation of the user's unit according to this document.
4. Circuitry and other examples described herein are meant merely to indicate the characteristics and performance of Hitachi's semiconductor products. Hitachi assumes no responsibility for any intellectual property claims or other problems that may result from applications based on the examples described herein.
5. No license is granted by implication or otherwise under any patents or other rights of any third party or Hitachi, Ltd.
6. **MEDICAL APPLICATIONS:** Hitachi's products are not authorized for use in MEDICAL APPLICATIONS without the written consent of the appropriate officer of Hitachi's sales company. Such use includes, but is not limited to, use in life support systems. Buyers of Hitachi's products are requested to notify the relevant Hitachi sales offices when planning to use the products in MEDICAL APPLICATIONS.

HITACHI

Hitachi, Ltd.

Semiconductor & IC Div.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100, Japan
Tel: Tokyo (03) 3270-2111
Fax: (03) 3270-5109

For further information write to:

Hitachi America, Ltd.
Semiconductor & IC Div.
2000 Sierra Point Parkway
Brisbane, CA. 94005-1835
U S A
Tel: 415-589-8300
Fax: 415-583-4207

Hitachi Europe GmbH
Continental Europe
Dornacher Straße 3
D-85622 Feldkirchen
München
Tel: 089-9 91 80-0
Fax: 089-9 29 30-00

Hitachi Europe Ltd.
Electronic Components Div.
Northern Europe Headquarters
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA
United Kingdom
Tel: 01628-585000
Fax: 01628-585160

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.
Unit 706, North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon
Hong Kong
Tel: 27359218
Fax: 27306071

Copyright © Hitachi, Ltd., 1997. All rights reserved. Printed in Japan.

HB56UW1673E-A Series

Revision Record

Rev.	Date	Contents of Modification	Drawn by	Approved by
0.0	Sep. 17, 1997	Initial issue (referred to HM5164405A/HM5165405A Series Rev. 1.0)		
